

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	I _D Τ _A = +25°C
20V	$0.55\Omega @ V_{GS} = 4.5V$	540mA

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

Load Switch

Features

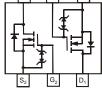
- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Alloy 42
 Leadframe. Solderable per MIL-STD-202, Method 208(3)
- Weight: 0.006 grams (Approximate)







Top View

Top View Internal Schematic

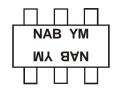
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2004DWK-7	SOT363	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



 $\begin{aligned} &\mathsf{NAB} = \mathsf{Product} \; \mathsf{Type} \; \mathsf{Marking} \; \mathsf{Code} \\ &\underline{\mathsf{YM}} = \mathsf{Date} \; \mathsf{Code} \; \mathsf{Marking} \\ &\overline{\mathsf{Y}} \; \mathsf{or} \; \mathsf{Y} = \mathsf{Year} \; (\mathsf{ex:} \; \mathsf{A} = 2013) \\ &\mathsf{M} = \mathsf{Month} \; (\mathsf{ex:} \; 9 = \mathsf{September}) \end{aligned}$

Date Code Key

Year	2006	2007		2013	2014	2015	2016	2017	2018	2019	2020	2021
Code	Т	U		Α	В	С	D	Е	F	G	Н	ı
Month	Jan	Feb	Mar	Apr	Mav	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Char	acteristic		Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±8	V
Drain Current (Note 5)	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$	I _D	540 390	mA
Pulsed Drain Current (Note 6)			I _{DM}	1.5	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	200	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-65 to +150	°C

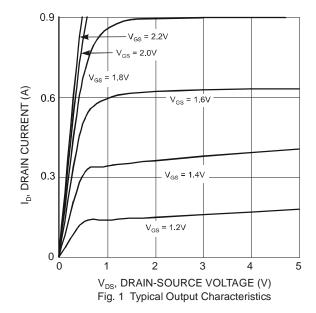
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

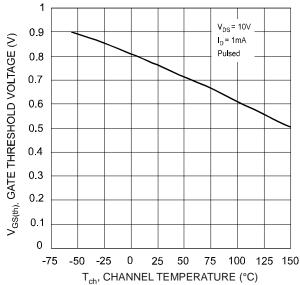
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V$, $I_D = 10\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	ı	-	1	μA	$V_{DS} = 16V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	=	=	±1	μA	$V_{GS} = \pm 4.5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(th)}$	0.5	-	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
			0.4	0.55		$V_{GS} = 4.5V, I_D = 540mA$	
Static Drain-Source On-Resistance	R _{DS (ON)}	-	0.5	0.70	Ω	$V_{GS} = 2.5V, I_D = 500mA$	
			0.7	0.9		$V_{GS} = 1.8V, I_D = 350mA$	
Forward Transfer Admittance	Y _{fs}	200	=	-	mS	$V_{DS} = 10V, I_D = 0.2A$	
Diode Forward Voltage (Note 7)	V_{SD}	0.5	=	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss	-	36	150	pF	l.,,	
Output Capacitance	Coss	-	5.7	25	pF	$V_{DS} = 16V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	-	4.2	20	pF		
Total Gate Charge (V _{GS} = 4.5V)	Q_g	=	0.53	-			
Total Gate Charge (V _{GS} = 8.0V)	Q_g	-	0.95	-	nC	\/ 40\/ L 250m A	
Gate-Source Charge	Q _{gs}	-	0.08	-	- IIC	$V_{DS} = 10V, I_D = 250mA$	
Gate-Drain Charge	Q_{gd}	-	0.07	-			
Turn-On Delay Time	t _{D(on)}	=	4.1	-	ns		
Turn-On Rise Time	t _r	-	7.3	-	ns	$V_{DD} = 10V, R_L = 47\Omega,$	
Turn-Off Delay Time	t _{D(off)}	-	13.8	-	ns	$V_{GEN} = 4.5V$, $R_{GEN} = 10\Omega$	
Turn-Off Fall Time	t _f	-	10.5	-	ns		

Notes: 5. Device mounted on FR-4 PCB.

6. Pulse width ≤10µS, Duty Cycle ≤1%.
7. Short duration pulse test used to minimize self-heating effect.







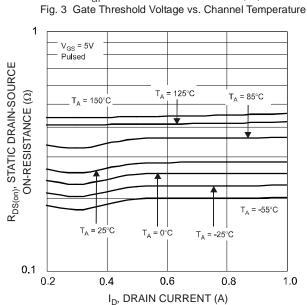


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

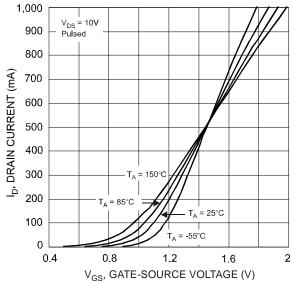


Fig. 2 Reverse Drain Current vs. Source-Drain Voltage

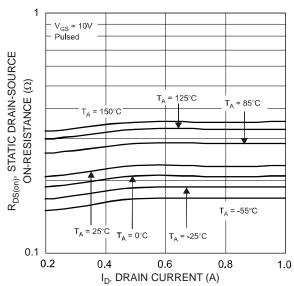


Fig. 4 Static Drain-Source On-Resistance Vs. Drain Current

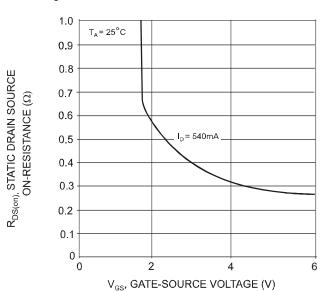


Fig. 6 Static Drain-Source, On-Resistance vs. Gate-Source Voltage



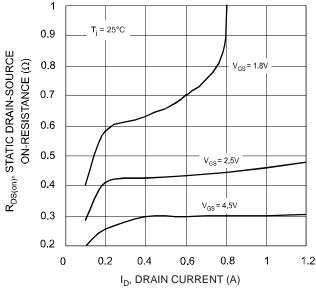
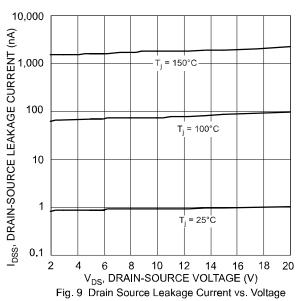


Fig. 7 On-Resistance vs. Drain Current and Gate Voltage



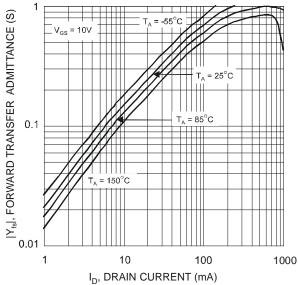
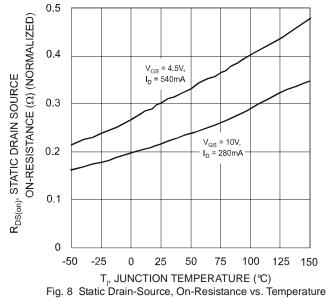


Fig. 11 Forward Transfer Admittance vs. Drain Current



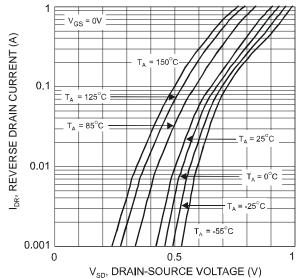
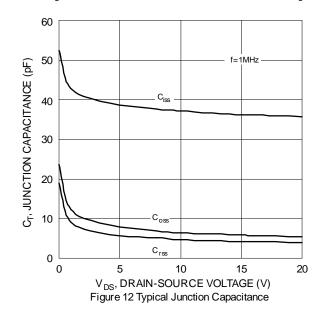
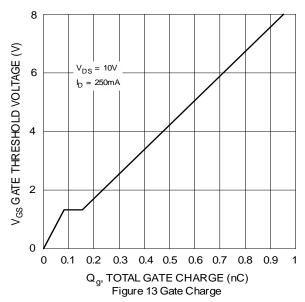
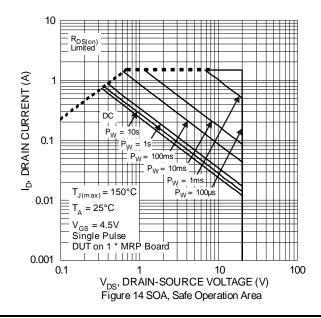


Fig. 10 Reverse Drain Current vs. Source-Drain Voltage



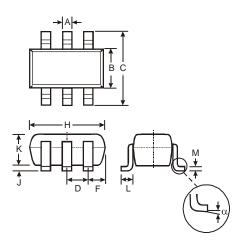






Package Outline Dimensions

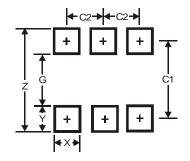
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT363						
Dim	Min	Max	Тур			
Α	0.10	0.30	0.25			
В	1.15	1.35	1.30			
С	2.00	2.20	2.10			
D		0.65 Ty	/p			
F	0.40	0.45	0.425			
Н	1.80	2.20	2.15			
J	0	0.10	0.05			
K	0.90	1.00	1.00			
L	0.25	0.40	0.30			
M	0.10	0.22	0.11			
α	0°	8°	-			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	SOT363
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65



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